PBSS9110T

100 V, 1 A PNP low VCEsat transistor

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS8110T

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat} and corresponding low RCEsat
- High collector current capability
- · High collector current gain
- · Improved efficiency due to reduced heat generation
- AEC-Q101 qualified

3. Applications

- Major application segments
 - Automotive 42 V power
 - · Telecom infrastructure
 - Industrial
- DC/DC converters
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|------|------|
| V _{CEO} | collector-emitter voltage | open base | - | - | -100 | V |
| I _C | collector current | | - | - | -1 | Α |
| I _{CM} | peak collector current | limited by T _{j(max)} | - | - | -3 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = -1 A; I_B = -100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 170 | 320 | mΩ |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | В | base | 3 | _ |
| 2 | Е | emitter | | C |
| 3 | С | collector | | В |
| | | | | E sym132 |
| | | | SOT23 | • ' |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| PBSS9110T | SOT23 | plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body | SOT23 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBSS9110T | %U7 |

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

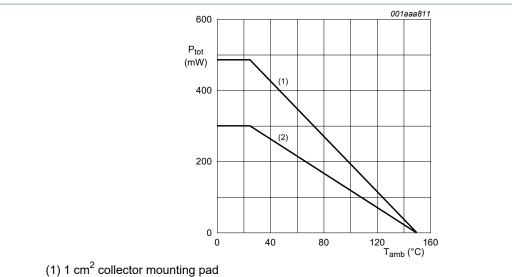
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|--------------------------------|-----|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | -120 | V |
| V_{CEO} | collector-emitter voltage | open base | | - | -100 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | -5 | V |
| I _C | collector current | | | - | -1 | Α |
| I _{CM} | peak collector current | limited by T _{j(max)} | | - | -3 | Α |
| I _B | base current | | | - | -300 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 300 | mW |
| | | | [2] | - | 480 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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- - (2) Standard footprint

Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------|-------------------------|-------------|-----|-----|-----|-----|------|
| uily-a) | thermal resistance from | in free air | [1] | - | - | 417 | K/W |
| | junction to ambient | | [2] | - | - | 260 | K/W |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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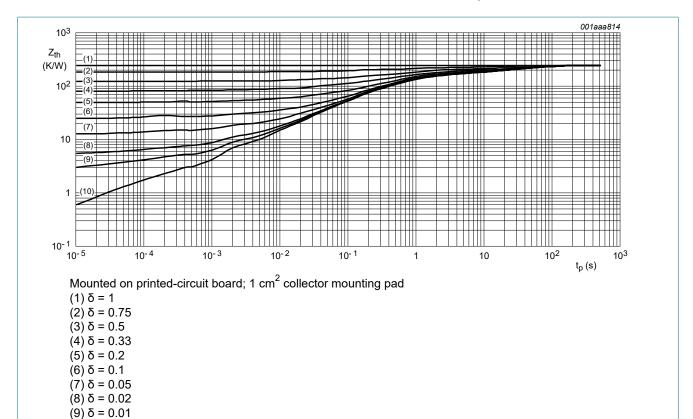
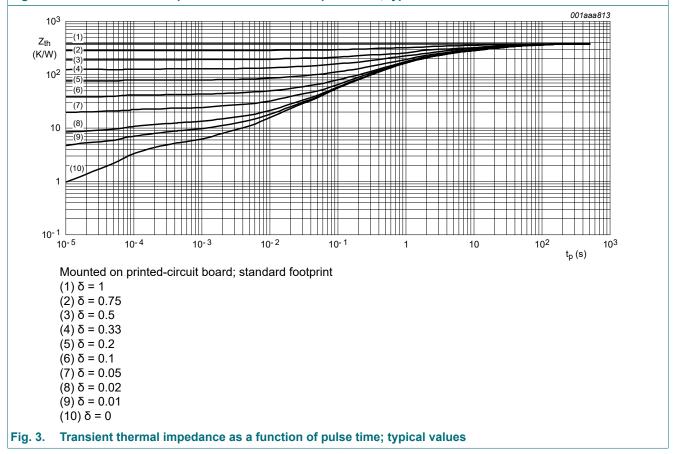


Fig. 2. Transient thermal impedance as a function of pulse time; typical values

 $(10) \delta = 0$



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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------------------|---|---|------|------|------|------|
| $V_{(BR)CBO}$ | collector-base breakdown voltage | $I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$ | -120 | - | - | V |
| V _{(BR)CEO} | collector-emitter breakdown voltage | I_C = -10 mA; I_B = 0 A; T_{amb} = 25 °C | -100 | - | - | V |
| V _{(BR)EBO} | emitter-base breakdown voltage (collector open) | I _C = 0 A; T _{amb} = 25 °C | -5 | - | - | V |
| I _{CBO} | collector-base cut-off | V _{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C | - | - | -100 | nA |
| | current | V _{CB} = -80 V; I _E = 0 A; T _j = 150 °C | - | - | -50 | μΑ |
| I _{CES} | collector-emitter cut-off current | V _{CE} = -80 V; V _{BE} = 0 V; T _{amb} = 25 °C | - | - | -100 | nA |
| I _{EBO} | emitter-base cut-off current | V _{EB} = -4 V; I _C = 0 A; T _{amb} = 25 °C | - | - | -100 | nA |
| h _{FE} | DC current gain | V _{CE} = -5 V; I _C = -1 mA; T _{amb} = 25 °C | 150 | - | - | |
| | | V _{CE} = -5 V; I _C = -250 mA; T _{amb} = 25 °C | 150 | - | - | |
| | | V_{CE} = -5 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 150 | - | 450 | |
| | | V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 125 | - | - | |
| V _{CEsat} collector-emitter | I _C = -250 mA; I _B = -25 mA; T _{amb} = 25 °C | - | - | -120 | mV | |
| | saturation voltage | I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C | - | - | -180 | mV |
| | | I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ | - | - | -320 | mV |
| R _{CEsat} | collector-emitter saturation resistance | 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | 170 | 320 | mΩ |
| V _{BEsat} | base-emitter saturation voltage | I _C = -1 A; I _B = -100 mA; T _{amb} = 25 °C | - | - | -1.1 | V |
| V_{BEon} | base-emitter turn-on voltage | V _{CE} = -5 V; I _C = -1 A; T _{amb} = 25 °C | - | - | -1 | V |
| f _⊤ | transition frequency | V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C | 100 | - | - | MHz |
| C _c | collector capacitance | V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C | - | - | 17 | pF |

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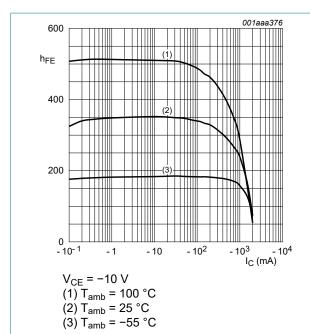


Fig. 4. DC current gain as a function of collector current; typical values

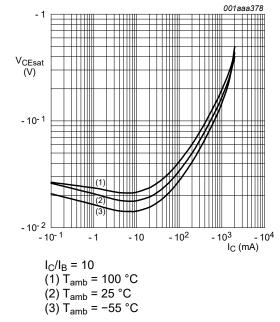


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

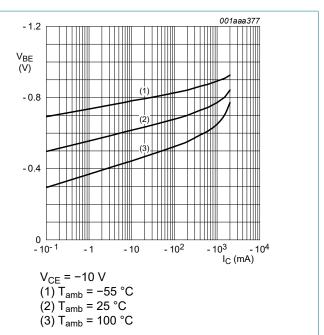


Fig. 5. Base-emitter voltage as a function of collector current; typical values

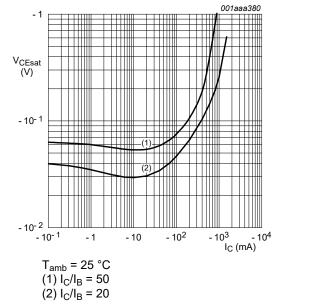


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

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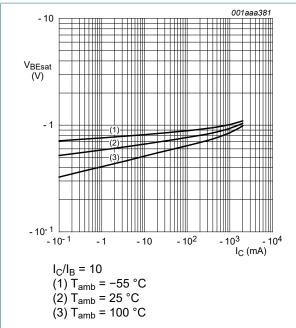


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

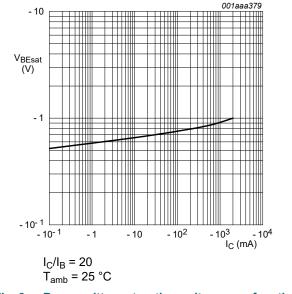


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

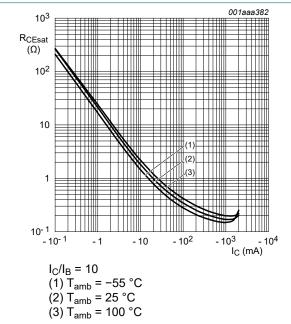


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

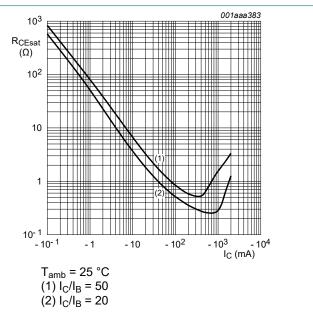


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

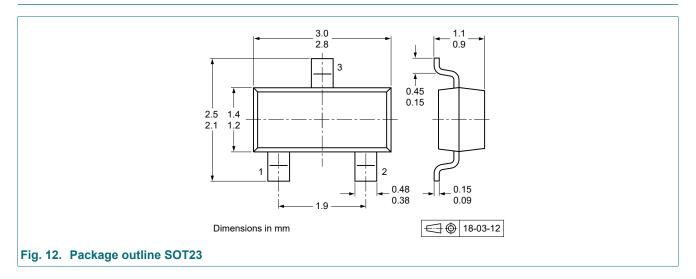
11. Test information

Quality information

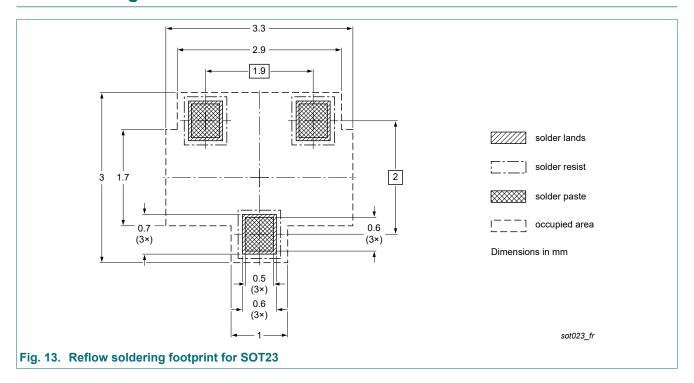
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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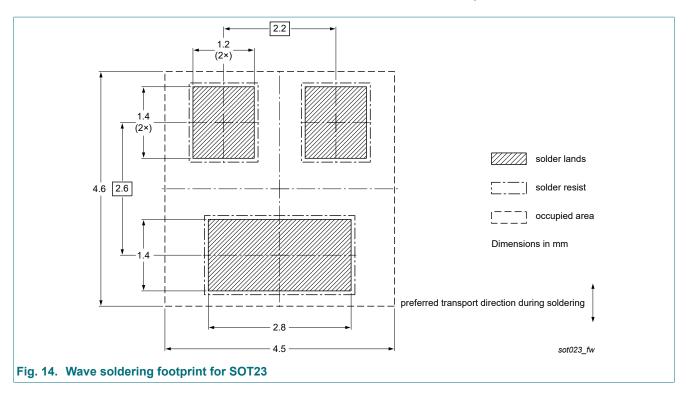
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | | |
|----------------|--------------|---|---------------|---------------|--|--|--|--|
| PBSS9110T v.3 | 20220523 | Product data sheet | - | PBSS9110T v.2 | | | | |
| Modifications: | guidelines | The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. | | | | | | |
| PBSS9110T v.2 | 20040513 | Product data sheet | - | PBSS9110T v.1 | | | | |
| PBSS9110T v.1 | 20040506 | Product data sheet | - | - | | | | |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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